

# GAGG

(Gd<sub>3</sub>Al<sub>2</sub>Ga<sub>3</sub>O<sub>12</sub> (Ce))

High light output &  
High energy resolution &  
Non hygroscopic nature  
Scintillator

Patent No.:EP2671940(B1), US8969812(B2), RU2622124(C2), JP5952746(B2)  
EP3138891(B1), US10174247(B2), RU2670919(C9)



## Product Information

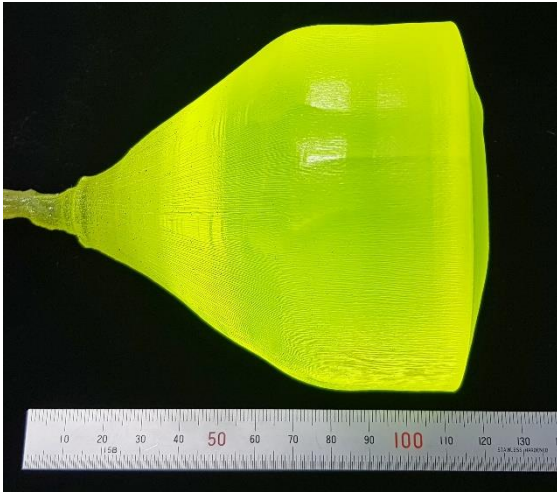


Fig.1 photograph of 4-inch-diameter GAGG scintillator.\*<sup>1</sup>

\*<sup>1</sup> Czochralski growth of 4-inch diameter Ce:Gd<sub>3</sub>Al<sub>2</sub>Ga<sub>3</sub>O<sub>12</sub> single crystals for scintillator applications  
V.Kochurikhin et al., J.Cryst.Growth, 531 (2020) 125384.

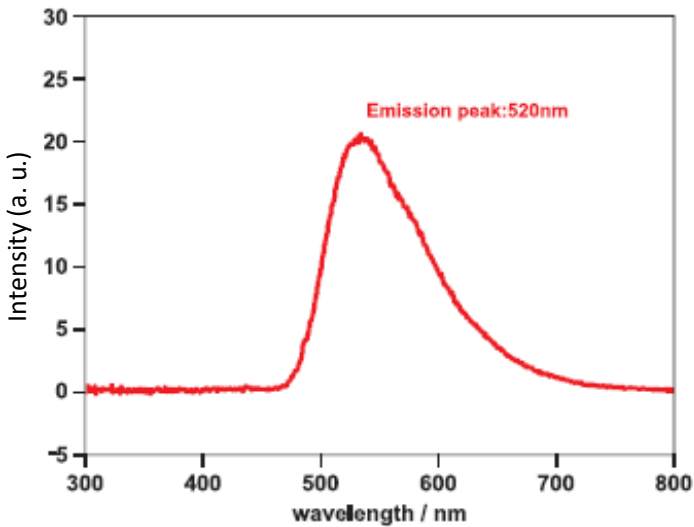


Fig.2: Radioluminescence spectra of GAGG excited by X-ray, CuK $\alpha$ , 120 $\mu$ A, 40kV

## Outline

GAGG scintillator has high light output, high energy resolution and high density among oxide scintillators. GAGG has no hygroscopic and no self radiation nature.

4-inch-diameter GAGG bulk single crystal was achieved.

We can supply the variety of the GAGG shape.

Cube, array, plate, cylinder, rod, wafer etc... are available.

## Scintillation Properties\*<sup>2</sup>

Light output [photons/MeV]	45,000~ 55,000
Energy resolution (662 keV, FWHM) [%]	8~9
Decay time [ns]	~90
Emission wavelength [nm]	520
Density [g/cm <sup>3</sup> ]	6.63

\*<sup>2</sup> All properties were measured using 5 x 5 x 5 mm<sup>3</sup> sample.